

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

LM358QT-MS

Product specification

产品简介

LM358QT-MS 是一款双路低功耗的差分式运算放大器，可以单电源或双电源供电。具有较高的开环增益、内部补偿、高共模范围和良好的温度稳定性，以及具有输出短路保护的特点。广泛应用于传感器的放大电路、直流放大模块、音频放大电路和传统的运算放大电路中。

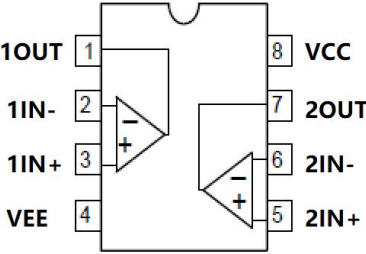
产品特点

- 内部频率补偿
- 短路保护
- 低功耗：典型值 0.5mA @ $V_{\alpha}=5V$
- 封装形式：
- 单电源电压范围：3V~36V
- 双电源电压范围：±18V
- 单位增益带宽:可达 1.2MHZ

产品用途

- 传感器信号放大器
- 直流增益
- 音频放大器
- 其它应用领域

产品概要及封装信息

DFN-8-EP(2x2)	引脚配置	管体标记
		

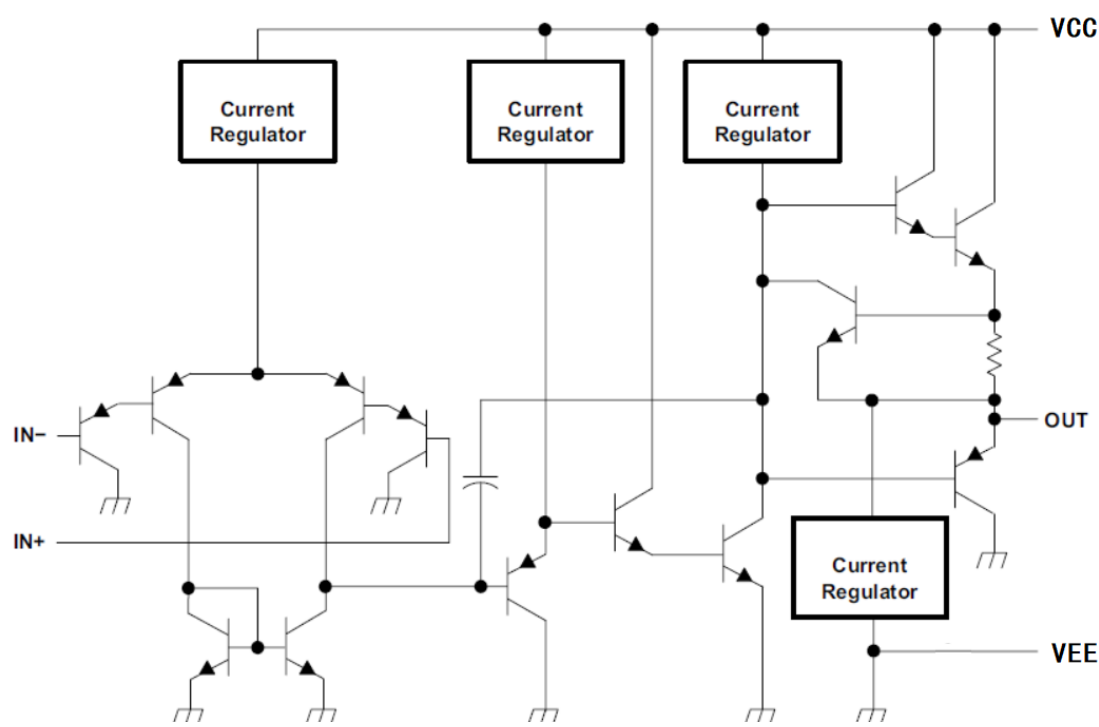
Order information

封装	型号	包装数量
DFN-8-EP(2x2)	LM358QT-MS	Tape and Reel,4000

管脚功能定义

管脚序号	管脚定义	功能说明
1	1OUT	第 1 路运放输出
2	1IN-	第 1 路运放反相输入
3	1IN+	第 1 路运放正相输入
4	VEE	负电源
5	2IN+	第 2 路运放正相输入
6	2IN-	第 2 路运放反相输入
7	2OUT	第 2 路运放输出
8	VCC	正电源

等效原理图



极限参数

项目	符号	极限值 ⁽¹⁾	单位
单电源供电电压	V _{cc}	40	V
双电源供电电压	V _s	±20	V
差分输入电压 ⁽²⁾	V _{ID}	±40	V
共模输入电压	V _{ICR}	-0.3~40V	V
输出短路时间	t _{sc}	连续	
耗散功率	P _D	400	mW
工作温度	T _A	-20° ~70°	°C
储存温度	T _S	-65-150	°C
焊接温度	T _w	260, 10s	°C

注:(1) 极限值是指无论在任何条件下都不能超过的极限值。如果达到此极限值,将有可能造成产品劣化等物理性 损伤;同时在接近极限参数下,不能保证芯片可以正常工作。

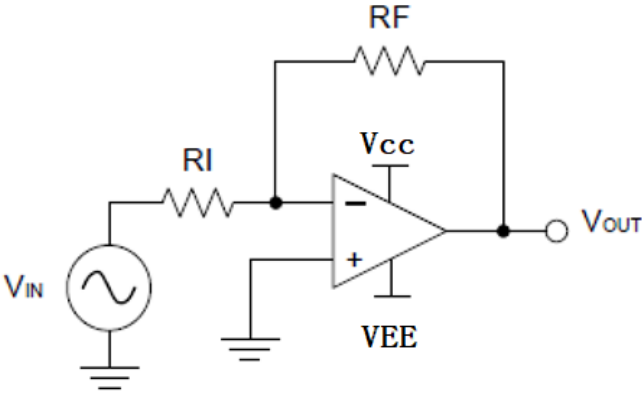
(2) 输入端IN+相对于IN-之间的电压差。

直流电学特性 ($T_A=25^{\circ}\text{C}$, $V_{CC}=5\text{V}$, $V_{EE}=\text{GND}$ 除非特别指定)

项目	符号	测试条件		最小值	典型值	最大值	单位
输入失调电压	V_{IO}	$V_{CC}=5\text{V}$ to MAX, $V_{IC}=V_{ICR}(\text{min})$, $V_O=1.4\text{V}$		–	5	–	mV
输入失调电流	I_{IO}	$V_O = 1.4\text{V}$		–	10	50	nA
偏置电流	I_{BIAS}	$V_O = 1.4\text{V}$		–	50	250	nA
共模输入电压	V_{ICR}	$V_{CC}=5\text{V}$ to 36V		V_{EE}	–	$V_{CC}-1.5\text{V}$	V
开环电压增益	A_{OL}	$V_{CC}=15\text{V}$, $V_O=1\text{V}$ to 11V, $R_L \geq 2\text{k}\Omega$			100	–	V/mV
共模抑制比	CMRR	$V_{CC}=5\text{V}$ to MAX, $V_{IC}=V_{ICR}(\text{min})$		–	80	–	dB
单位增益带宽	GBWP			–	1.2	–	MHZ
电源电压抑制比 P_{SSR}	$\Delta V_{VDD}/\Delta V_{IO}$	$V_{CC}=5\text{V}$ to MAX, $f=20\text{kHz}$		–	90	–	dB
串扰衰减抑制比 CS	V_{O1}/V_{O2}	$f=1\text{kHz}$ to 20kHz		–	120	–	dB
输出高电平电压	V_{OH}	$V_{CC}=15\text{V}$, $V_{ID}=1\text{V}$	$I_{out} = -50\mu\text{A}$	–	13.6	–	V
			$I_{out} = -1\text{mA}$	–	13.5	–	V
			$I_{out} = -5\text{mA}$	–	13.4	–	V
		$V_{CC}=28\text{V}$	$R_L=2\text{k}$		26	–	V
输出低电平电压	V_{OL}	$V_{CC}=15\text{V}$, $V_{ID}=-1\text{V}$	$I_{out} = 50\mu\text{A}$	–	0.1	–	V
			$I_{out} = 1\text{mA}$	–	0.7	–	V
			$I_{out} = 5\text{mA}$	–	1.0	–	V
		$V_{CC}=28\text{V}$	$R_L=2\text{k}$	–	0.85	–	V
输出短路电流	I_{OS}	$V_{CC}=5\text{V}$, $V_{EE}=-5\text{V}$, $V_O=0\text{V}$		–	± 24	–	mA
电源工作电流	I_{CC}	$V_{CC}=5\text{V}$, $V_O=1/2V_{CC}$, No load		–	0.5	–	mA
		$V_{CC}=36$, $V_O=1/2V_{CC}$, No load		–	0.8	–	mA
单电源工作电压	V_{CC}	$V_{EE}=0\text{V}(\text{GND})$		3	–	36	V
双电源工作电压	V_S	V_{CC}, V_{EE}		–18	–	+18	V

典型应用

线路图



2、设计要求

必须选择大于输入电压范围和输出范围的电源电压。

例如，将信号源 VIN 从±0.5 V 放大到±1.8V。将电源设置为±5 V 足以适应此应用要求。

3、设计过程

根据公式(1) 计算放大倍数(增益) A_v

$$A_v = -V_O/V_{IN} \quad \text{-----(1)}$$

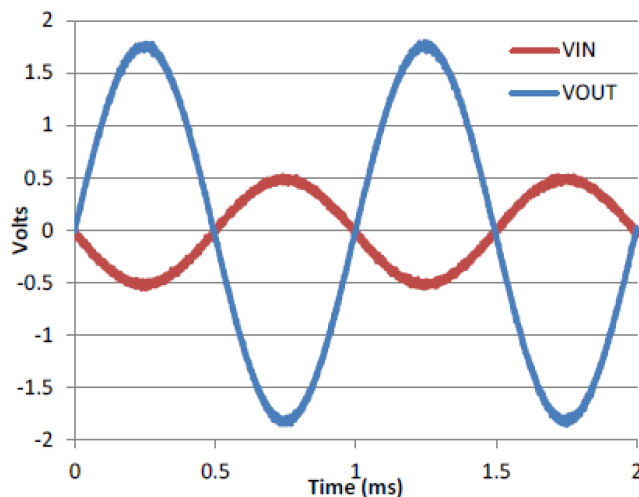
$$A_v = -V_O/V_{IN} = -1.8/0.5 = -3.6$$

一旦确定了所需的增益 A_v ，就要为 R_I 或 R_F 电阻选择一个值。根据运放的电特性及功耗的需要，可选择 1k Ω –100k Ω 范围内的值。本例将选择 $R_I=10\text{ k}\Omega$ ，则 $R_F=36\text{ k}\Omega$ 。这由方程式 2 确定。

$$A_v = -R_F/R_I \quad \text{-----(2)}$$

$$R_F = -A_v * R_I = 3.6 * 10 = 36\text{ k}\Omega$$

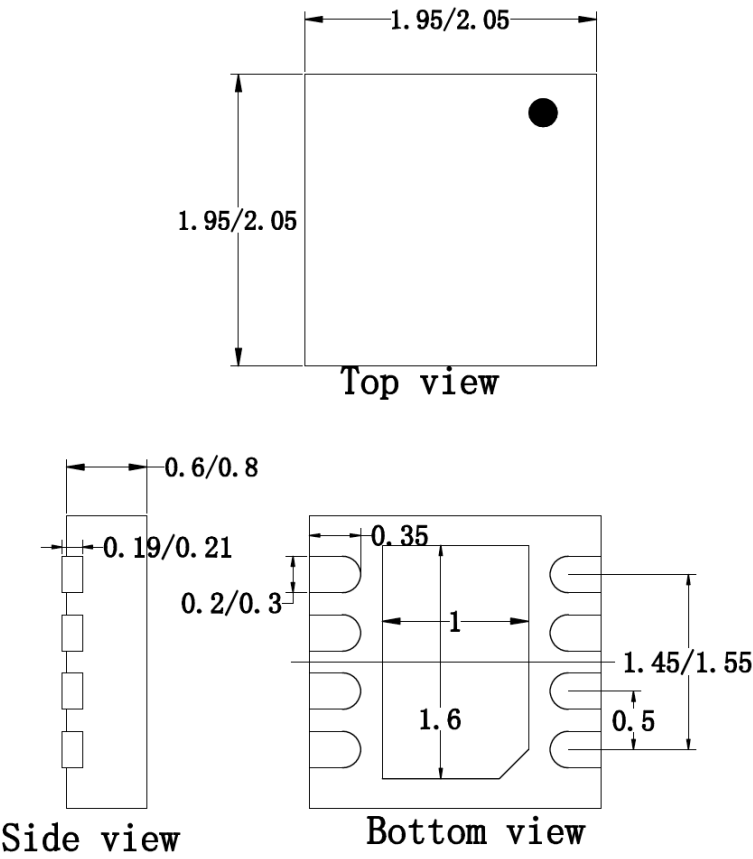
4、应用曲线图



反相放大器的输入电压 VS 输出电压

封装信息
DFN-8-EP(2x2)

单位：毫米



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